

1200 V 65 mΩ SiC MOSFET

Silicon Carbide MOSFET

Trench-Assisted Planar Technology

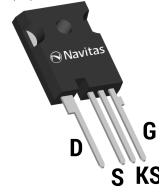
V_{DS}	=	1200 V
$R_{DS(ON)}(Typ.)$	=	65 mΩ
$I_D(T_C = 100^\circ C)$	=	25 A

Features

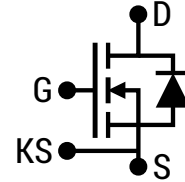
- Gen3F (3rd Generation) Technology
- Most Stable $R_{DS(ON)}$ over Temperature
- Low C_{OSS} , C_{RSS} and Balanced C_{ISS}/C_{RSS}
- Lower Q_{GD} and Balanced $R_{G(INT)}$
- Electromagnetically Optimized Design
- Robust Body Diode with Low V_F and Low Q_{RR}
- 100% Avalanche (UIL) Tested
- AEC-Q101 Qualified

Package

Case (D)



TO-247-4



D = Drain
G = Gate
S = Source
KS = Kelvin Source



Advantages

- Superior Performance and Robustness
- Lowest Conduction Losses at all Temperatures
- Lesser Switching Spikes and Lower Losses
- Faster and More Efficient Switching
- Reduced Ringing
- Ease of Paralleling without Thermal Runaway
- Excellent Power Density and System Efficiency
- Enhanced System Reliability

Applications

- xEV - OBC & DC-DC
- EV Fast Charging Infrastructure
- Solar / PV
- Energy Storage Systems
- Uninterruptible Power Supply
- Motor Control
- Induction Heating & Welding
- High Voltage Converters

Absolute Maximum Ratings (At $T_C = 25^\circ C$ Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Drain-Source Voltage	$V_{DS(max)}$	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	1200	V	
Gate-Source Voltage (Dynamic)	$V_{GS(max)}$		-10 / +22	V	
Gate-Source Voltage (Static)	$V_{GS(op)-ON}$	Recommended Operation	18	V	Note 1
	$V_{GS(op)-OFF}$		-5 to -3		
Continuous Drain Current	I_D	$T_C = 25^\circ C, V_{GS} = -5 / +18\text{ V}$	35	A	Fig. 16
		$T_C = 100^\circ C, V_{GS} = -5 / +18\text{ V}$	25		
		$T_C = 135^\circ C, V_{GS} = -5 / +18\text{ V}$	18		
Pulsed Drain Current	$I_{D(pulse)}$	$t_P \leq 3\text{ }\mu\text{s}, D \leq 1\%, V_{GS} = 18\text{ V}$	90	A	Note 2
Power Dissipation	P_D	$T_C = 25^\circ C$	153	W	Fig. 17
Non-Repetitive Avalanche Energy	E_{AS}	$L = 36\text{ mH}, I_{AV} = 3\text{ A}$	162	mJ	
Operating Junction and Storage Temperature	T_J, T_{stg}		-55 to 175	$^\circ C$	

Note 1: This product can support 0V turn-off gate drive voltage with optimized PCB layout and gate drive circuit configuration.

Note 2: Pulse Width t_P Limited by $T_{J(max)}$



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Electrical Characteristics (At $T_C = 25^\circ\text{C}$ Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	1200			V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$		1	50	μA	
Gate Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 22\text{ V}$			100	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = -10\text{ V}$			-100		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 10\text{ mA}$	2.2	3.1	4.3	V	Note 3
Transconductance	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 15\text{ A}$		8.3		S	Fig. 5
		$V_{DS} = 10\text{ V}, I_D = 15\text{ A}, T_j = 175^\circ\text{C}$		8.5			
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 18\text{ V}, I_D = 15\text{ A}$		65	86	m Ω	Fig. 6-9
		$V_{GS} = 18\text{ V}, I_D = 15\text{ A}, T_j = 175^\circ\text{C}$		122			
Input Capacitance	C_{iss}			1298		pF	Fig. 12
Output Capacitance	C_{oss}			53			
Reverse Transfer Capacitance	C_{rss}			4.5		μJ	Fig. 13
C_{oss} Stored Energy	E_{oss}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$ $f = 500\text{ KHz}, V_{AC} = 25\text{ mV}$		20			
C_{oss} Stored Charge	Q_{oss}			70		nC	
Effective Output Capacitance (Energy Related)	$C_{o(er)}$			62		pF	Note 4
Effective Output Capacitance (Time Related)	$C_{o(tr)}$			88			
Gate-Source Charge	Q_{gs}	$V_{DS} = 800\text{ V}, V_{GS} = -5 / +18\text{ V}$		15		nC	Fig. 11
Gate-Drain Charge	Q_{gd}	$I_D = 15\text{ A}$		16			
Total Gate Charge	Q_g	Per JEDEC JEP-192		55			
Internal Gate Resistance	$R_{G(int)}$	$V_{GS} = 18\text{ V}, f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$		1.3		Ω	
Turn-On Switching Energy (Body Diode)	E_{on}	$T_j = 25^\circ\text{C}, V_{GS} = -5/+18\text{ V}, R_{G(ext)} = 8\text{ }\Omega, L = 80.0\text{ }\mu\text{H}, I_D = 15\text{ A}, V_{DD} = 800\text{ V}$		116		μJ	Fig. 24-27
Turn-Off Switching Energy (Body Diode)	E_{off}			28			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 800\text{ V}, V_{GS} = -5/+18\text{ V}$ $R_{G(ext)} = 8\text{ }\Omega, L = 80.0\text{ }\mu\text{H}, I_D = 15\text{ A}$ Timing relative to V_{DS} , Inductive load		22		ns	Fig. 26
Rise Time	t_r			15			
Turn-Off Delay Time	$t_{d(off)}$			17			
Fall Time	t_f			10			

Note 3: Tested after applying 30ms pulse at $V_{GS} = +25\text{ V}$

Note 4: $C_{o(er)}$, a lumped capacitance that gives same stored energy as C_{oss} while V_{DS} is rising from 0 to 800V.

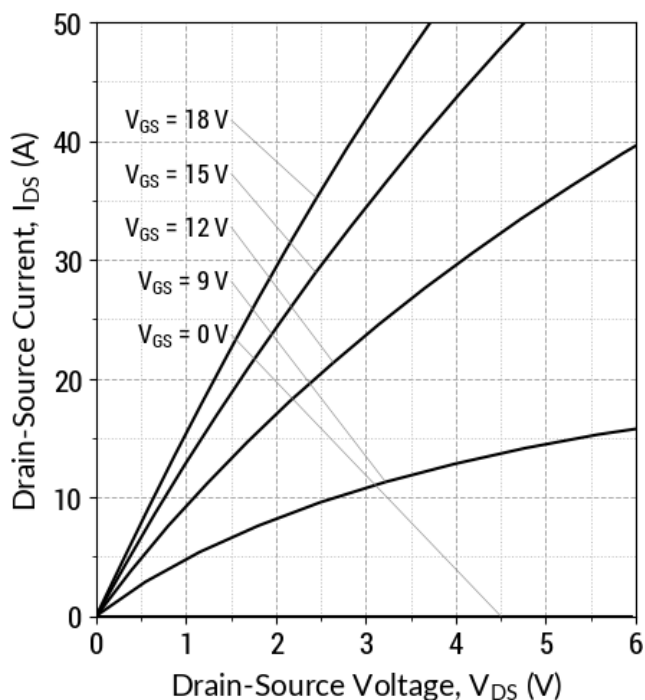
$C_{o(tr)}$, a lumped capacitance that gives same charging times as C_{oss} while V_{DS} is rising from 0 to 800V.

Reverse Diode Characteristics

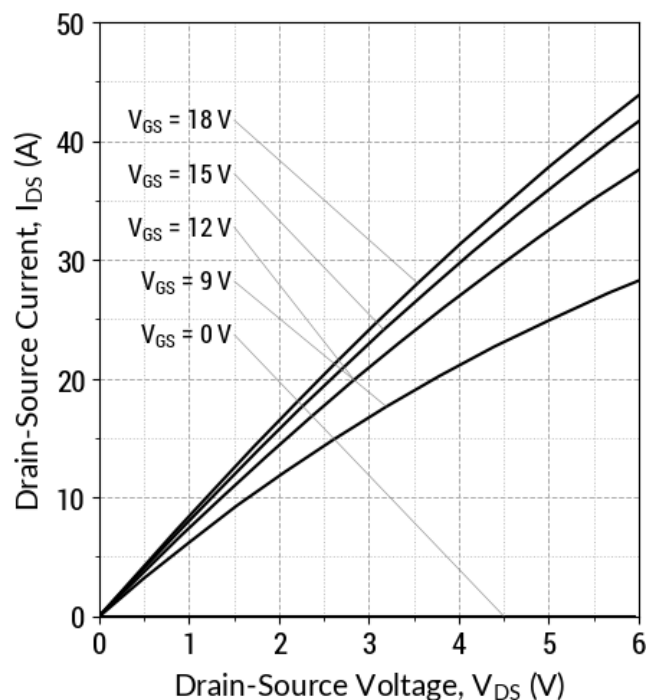
Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Diode Forward Voltage	V_{SD}	$V_{GS} = -5\text{ V}, I_{SD} = 7\text{ A}$ $V_{GS} = -5\text{ V}, I_{SD} = 7\text{ A}, T_j = 175^\circ\text{C}$		4.1 3.7		V	Fig. 18-19
Continuous Diode Forward Current	I_S	$V_{GS} = -5\text{ V}, T_c = 25^\circ\text{C}$ $V_{GS} = -5\text{ V}, T_c = 100^\circ\text{C}$			26 15	A	
Diode Pulse Current	$I_{S(pulse)}$	$V_{GS} = -5\text{ V}$		60		A	Note 2
Reverse Recovery Time	t_{rr}	$V_{GS} = -5\text{ V}, I_{SD} = 15\text{ A}, V_R = 800\text{ V}$ $dif/dt = 1000\text{ A}/\mu\text{s}, T_j = 25^\circ\text{C}$		15		ns	
Reverse Recovery Charge	Q_{rr}			64		nC	
Peak Reverse Recovery Current	I_{rm}			4.6		A	
Reverse Recovery Time	t_{rr}	$V_{GS} = -5\text{ V}, I_{SD} = 15\text{ A}, V_R = 800\text{ V}$ $dif/dt = 1000\text{ A}/\mu\text{s}, T_j = 175^\circ\text{C}$		23		ns	
Reverse Recovery Charge	Q_{rr}			160		nC	
Peak Reverse Recovery Current	I_{rm}			7		A	

Package Characteristics

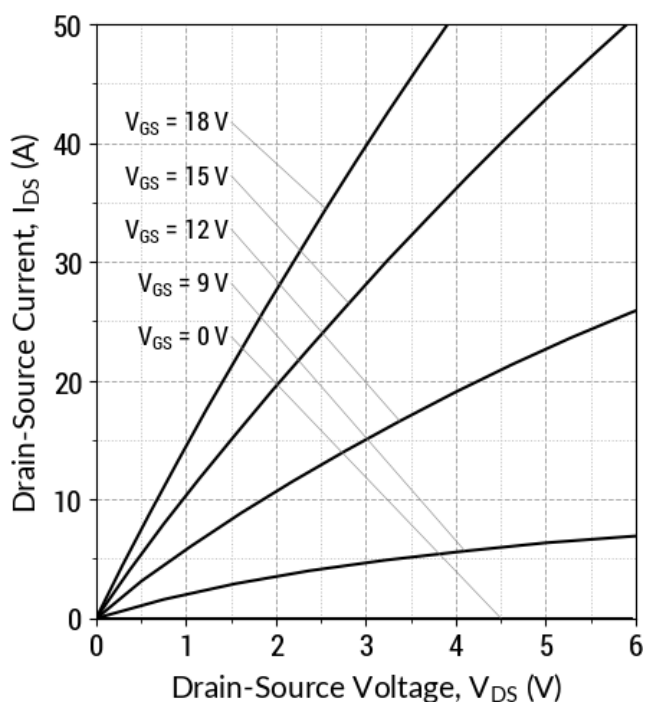
Parameter	Symbol	Conditions	Values	Unit	Note
Max Thermal Resistance, Junction - Case	$R_{thJC-Max}$	Maximum	0.98	$^\circ\text{C}/\text{W}$	Fig. 14
Weight	W_T		6.2	g	
Moisture Sensitivity Level	MSL		N/A		
EMC Material Group			II		
Max Mounting Torque	T_M	Screws to Heatsink	1.1	Nm	

Fig 1: Typical Output Characteristics ($T_j = 25^\circ\text{C}$)

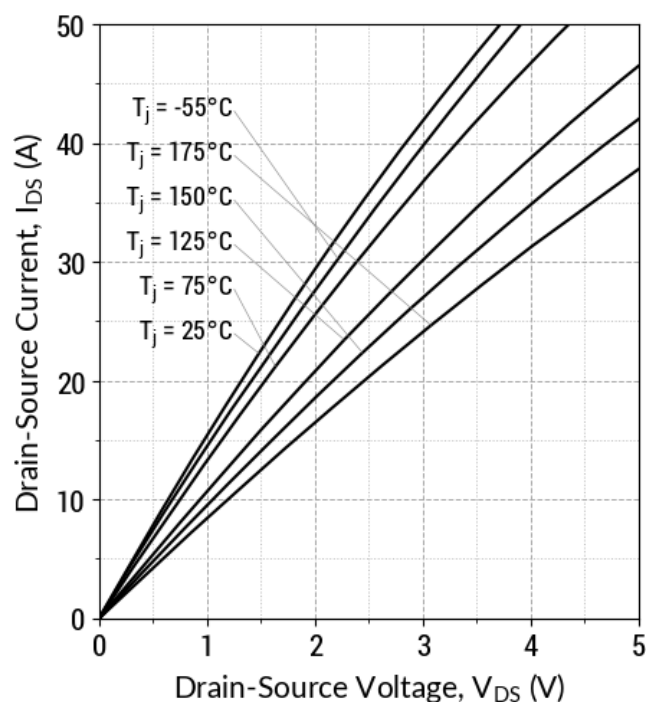
$$I_D = f(V_{DS}, V_{GS}); t_P = 50\ \mu\text{s}$$

Fig 2: Typical Output Characteristics ($T_j = 175^\circ\text{C}$)

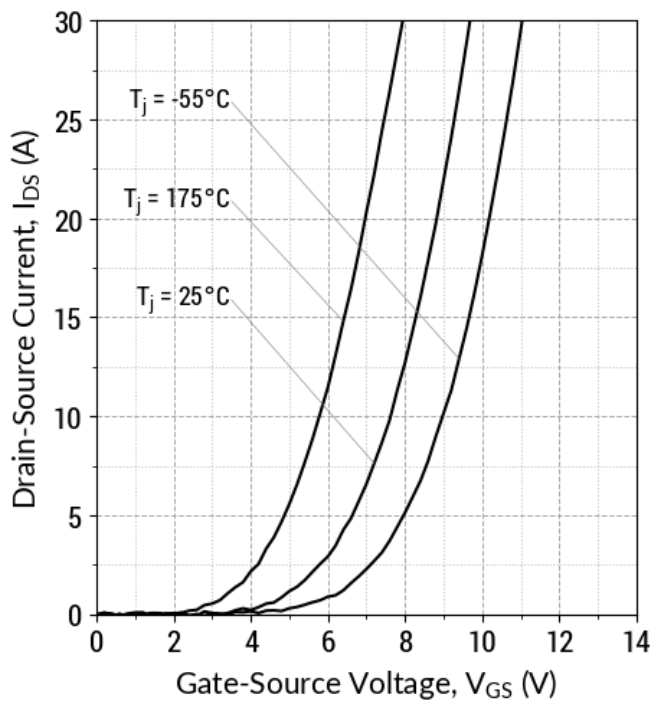
$$I_D = f(V_{DS}, V_{GS}); t_P = 50\ \mu\text{s}$$

Fig 3: Typical Output Characteristics ($T_j = -55^\circ\text{C}$)

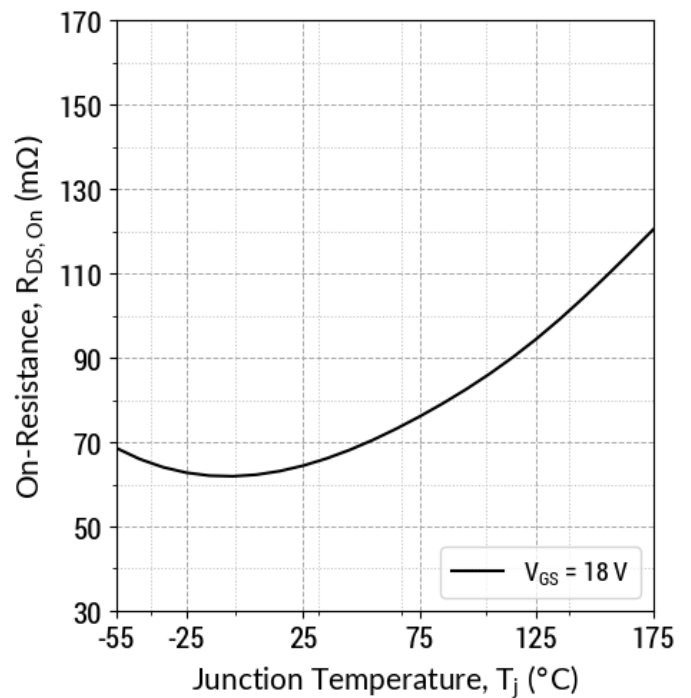
$$I_D = f(V_{DS}, V_{GS}); t_P = 50\ \mu\text{s}$$

Fig 4: Typical Output Characteristics ($V_{GS} = 18\text{ V}$)

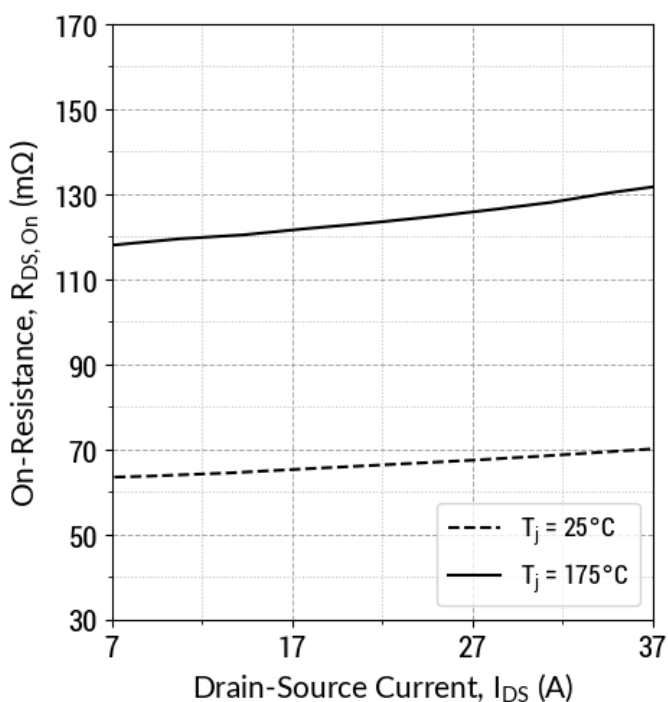
$$I_D = f(V_{DS}, T_j); t_P = 50\ \mu\text{s}$$

Fig 5: Typical Transfer Characteristics ($V_{DS} = 10\text{ V}$)

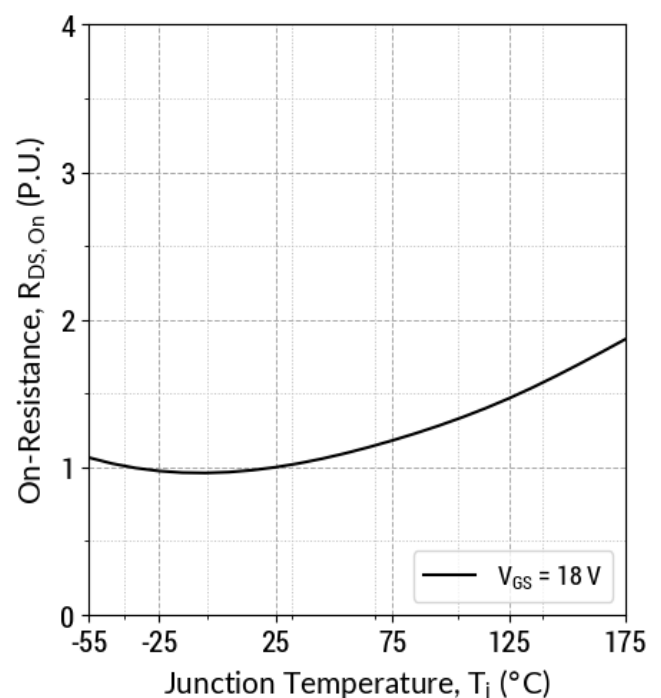
$$I_D = f(V_{GS}, T_j); t_P = 100\ \mu\text{s}$$

Fig 6: Typical $R_{DS(ON)}$ v/s Temperature

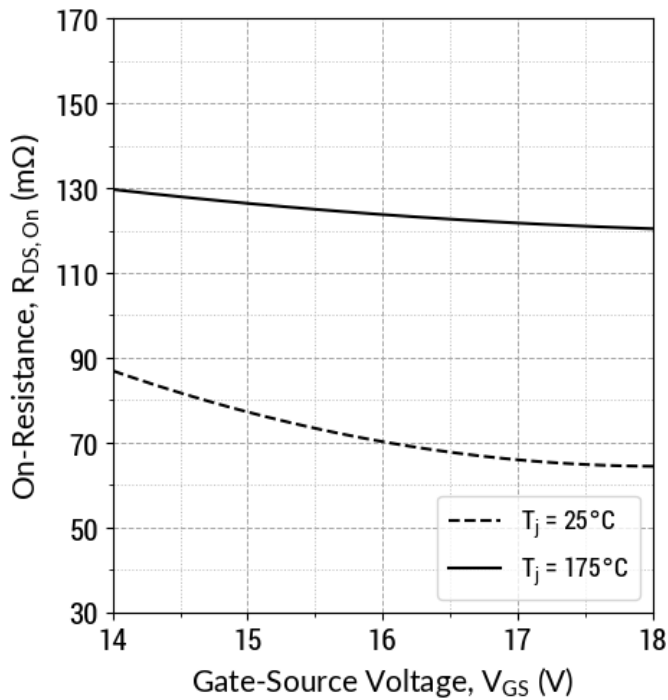
$$R_{DS(ON)} = f(T_j, V_{GS}); t_P = 50\ \mu\text{s}; I_D = 15\text{ A}$$

Fig 7: Typical $R_{DS(ON)}$ v/s Drain Current

$$R_{DS(ON)} = f(T_j, I_D); t_P = 50\ \mu\text{s}; V_{GS} = 18\text{ V}$$

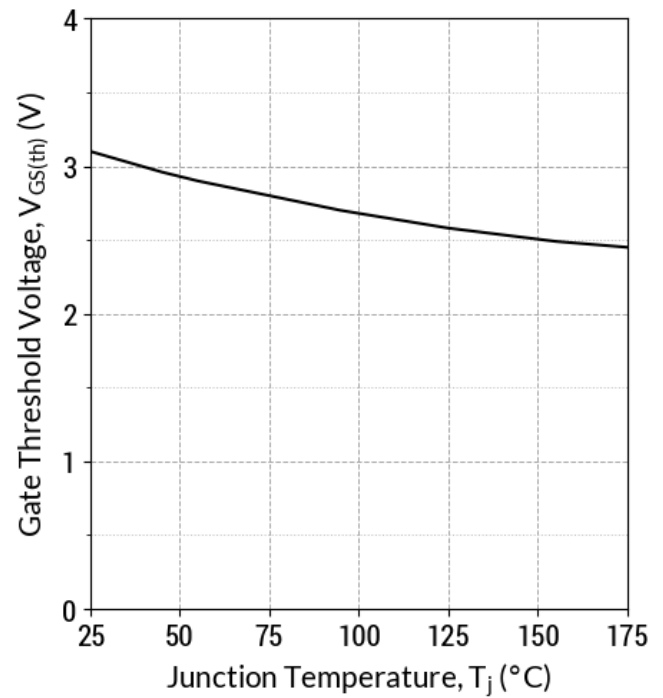
Fig 8: Typical Normalized $R_{DS(ON)}$ v/s Temperature

$$R_{DS(ON)} = f(T_j); t_P = 50\ \mu\text{s}; I_D = 15\text{ A}$$

Fig 9: Typical $R_{DS(ON)}$ v/s Gate Voltage

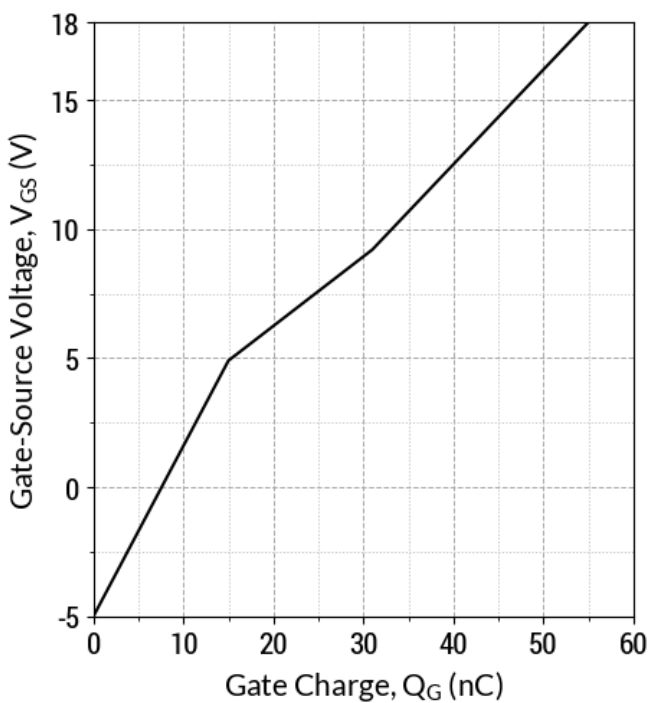
$$R_{DS(ON)} = f(T_j, V_{GS}); t_P = 50 \mu\text{s}; I_D = 15 \text{ A}$$

Fig 10: Typical Threshold Voltage Characteristics



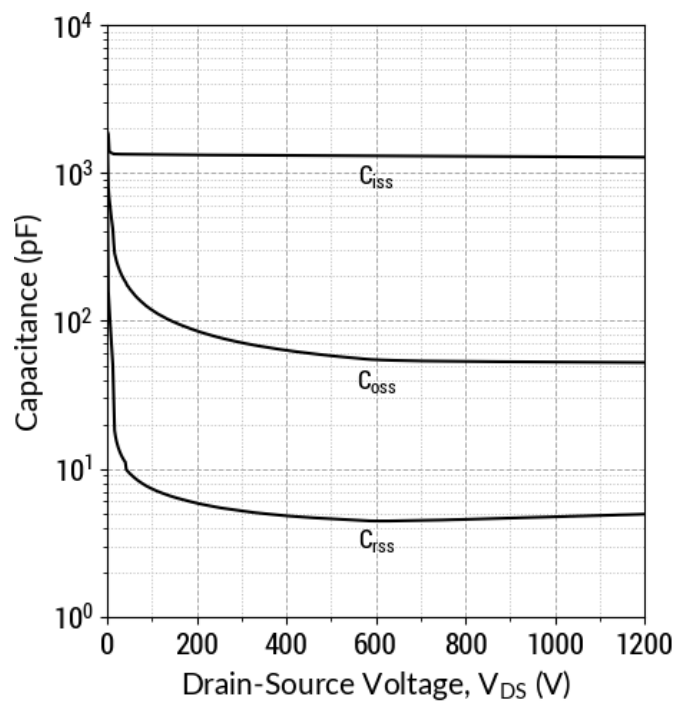
$$V_{GS(th)} = f(T_j); V_{DS} = V_{GS}; I_D = 10 \text{ mA}$$

Fig 11: Typical Gate Charge Characteristics



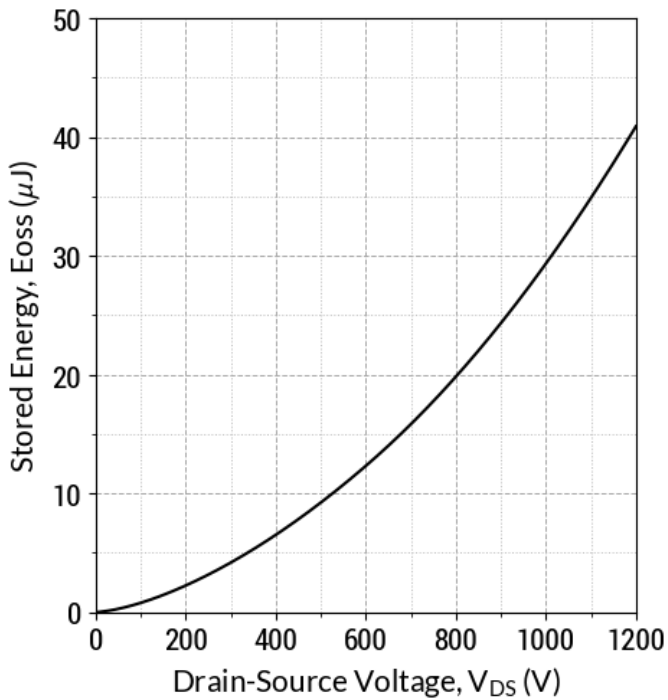
$$I_D = 15 \text{ A}; V_{DS} = 800 \text{ V}; T_c = 25^\circ\text{C}$$

Fig 12: Typical Capacitance v/s Drain-Source Voltage



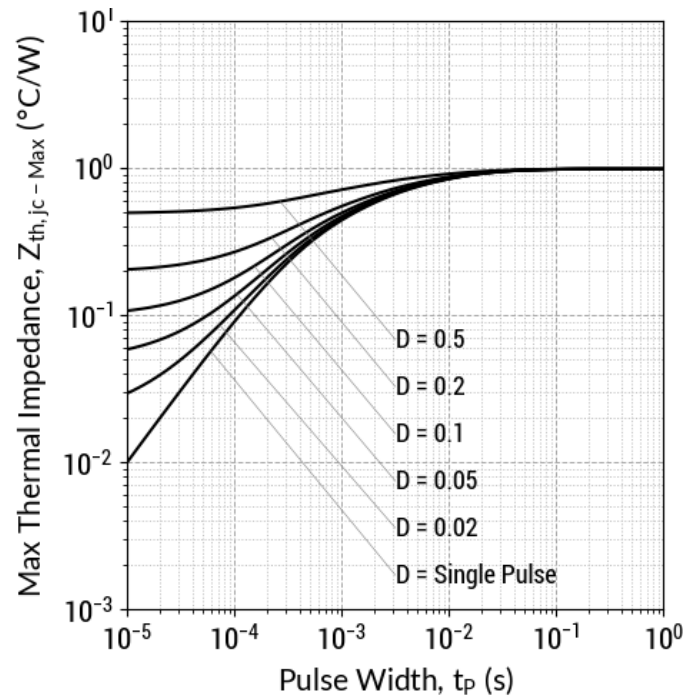
$$f = 500 \text{ KHz}; V_{AC} = 25 \text{ mV}$$

Fig 13: Output Capacitor Stored Energy

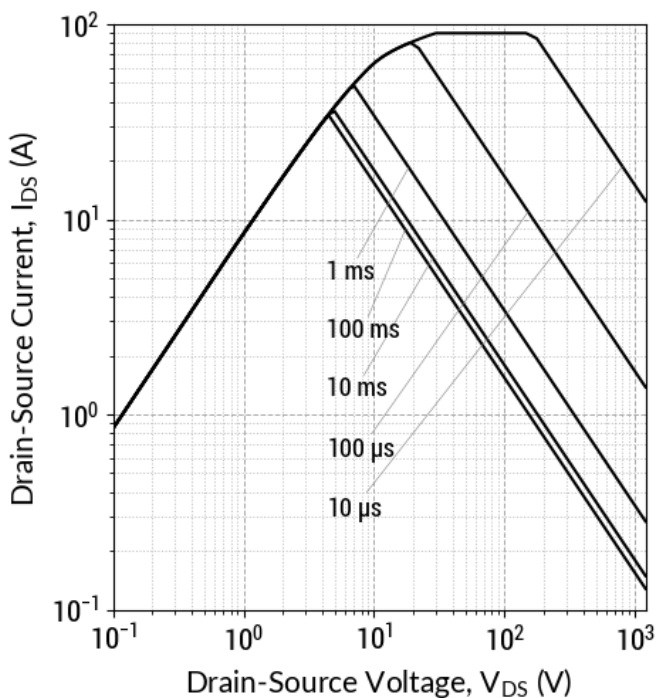


$$E_{oss} = f(V_{DS})$$

Fig 14: Max. Transient Thermal Impedance

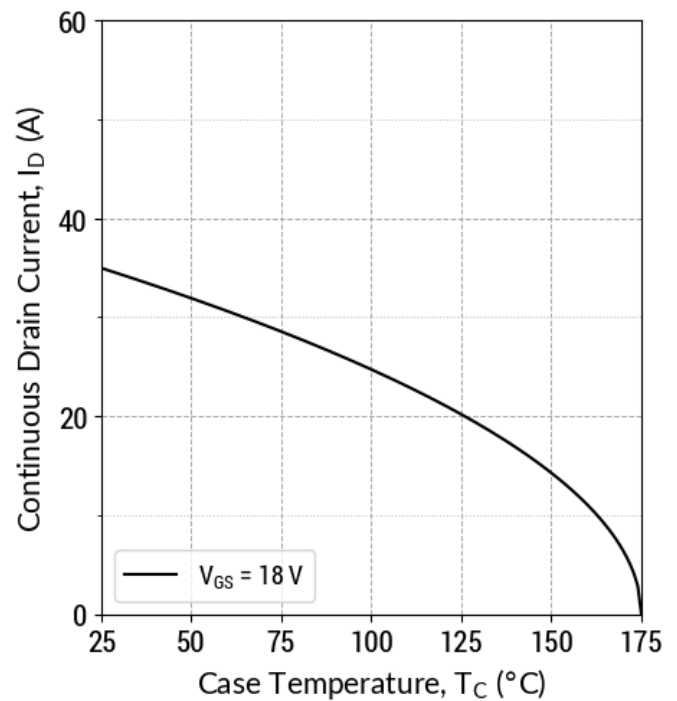


$$Z_{th,jc} = f(t_p, D); D = t_p/T$$

Fig 15: Safe Operating Area ($T_c = 25^{\circ}C$)

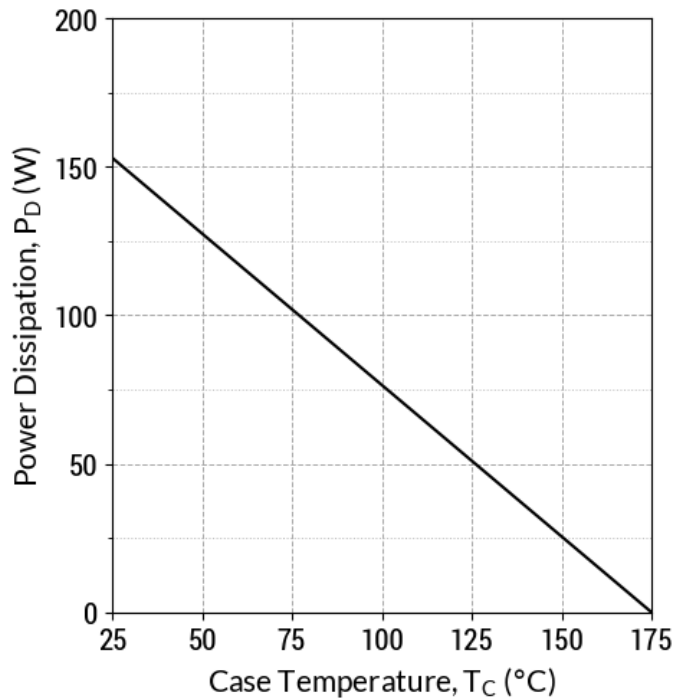
$$I_D = f(V_{DS}, t_p); T_j \leq 175^{\circ}C; D = 0$$

Fig 16: Current De-rating Curve

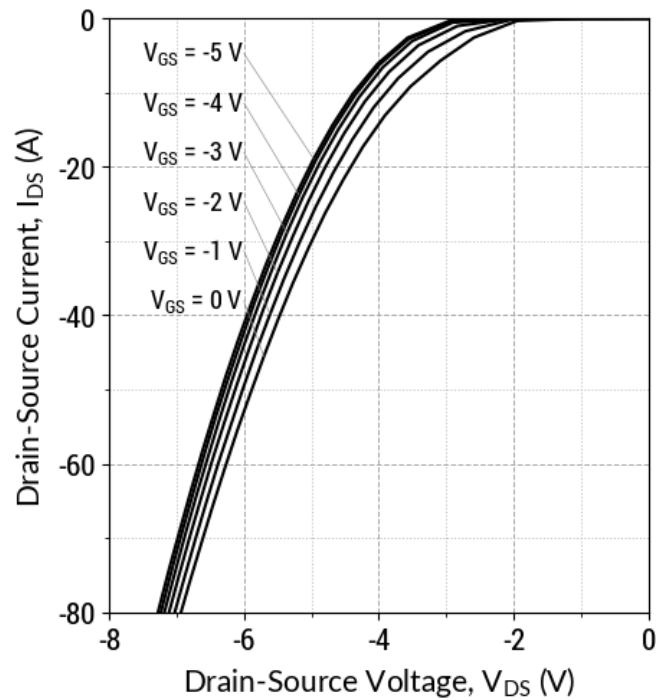


$$I_D = f(T_C); T_j \leq 175^{\circ}C$$

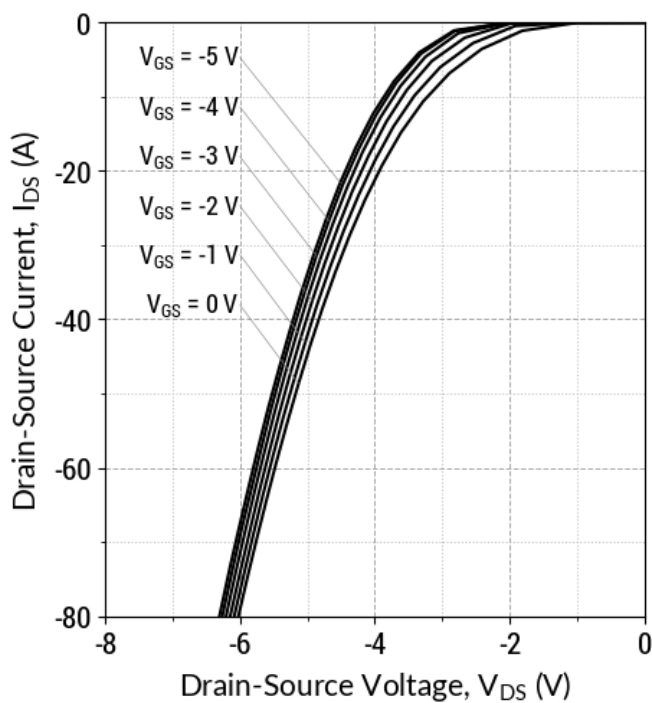
Fig 17: Power De-rating Curve



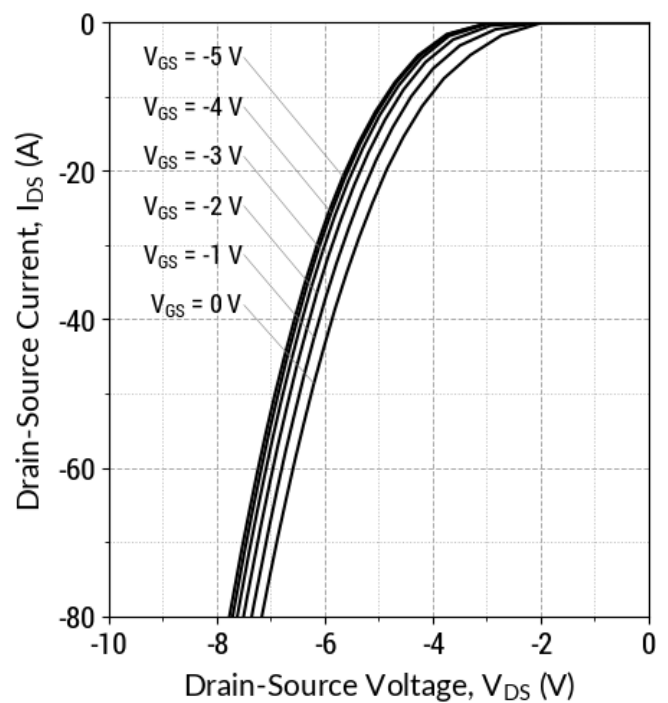
$$P_D = f(T_C); T_j \leq 175^\circ\text{C}$$

Fig 18: Typical Body Diode Characteristics ($T_j = 25^\circ\text{C}$)

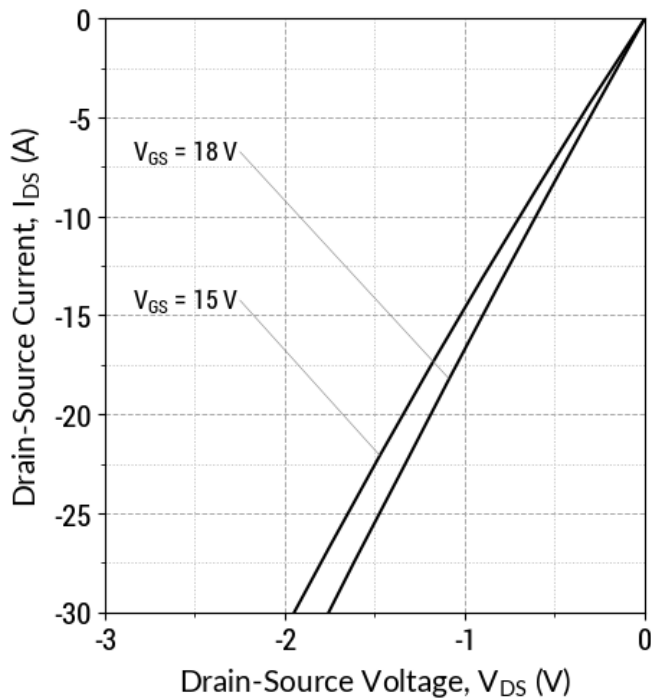
$$I_D = f(V_{DS}, V_{GS}); t_P = 50\text{ }\mu\text{s}$$

Fig 19: Typical Body Diode Characteristics ($T_j = 175^\circ\text{C}$)

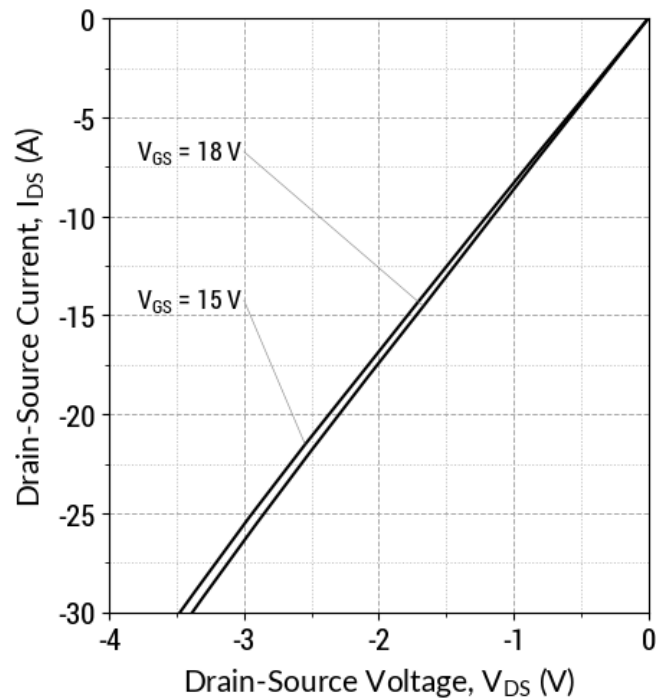
$$I_D = f(V_{DS}, V_{GS}); t_P = 50\text{ }\mu\text{s}$$

Fig 20: Typical Body Diode Characteristics ($T_j = -55^\circ\text{C}$)

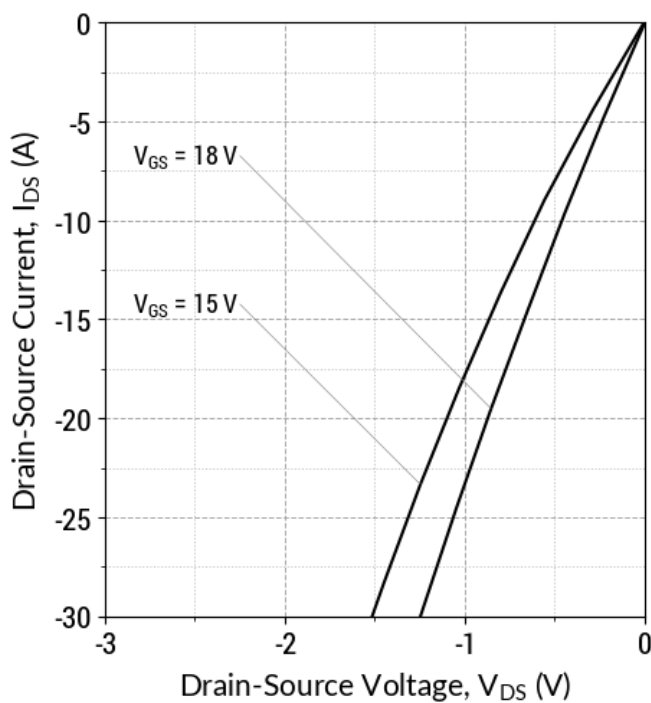
$$I_D = f(V_{DS}, V_{GS}); t_P = 50\text{ }\mu\text{s}$$

Fig 21: Typical Third Quadrant Characteristics ($T_j = 25^\circ\text{C}$)

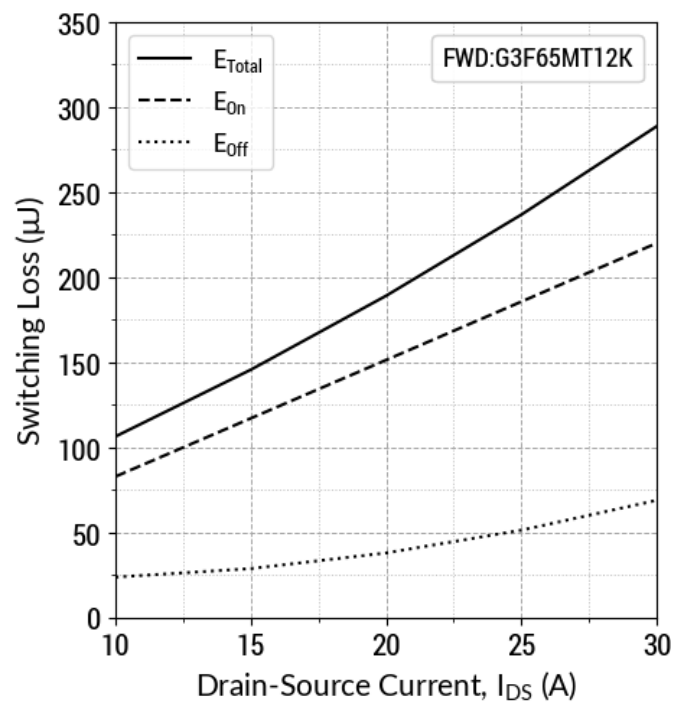
$$I_D = f(V_{DS}, V_{GS}); t_P = 50 \mu\text{s}$$

Fig 22: Typical Third Quadrant Characteristics ($T_j = 175^\circ\text{C}$)

$$I_D = f(V_{DS}, V_{GS}); t_P = 50 \mu\text{s}$$

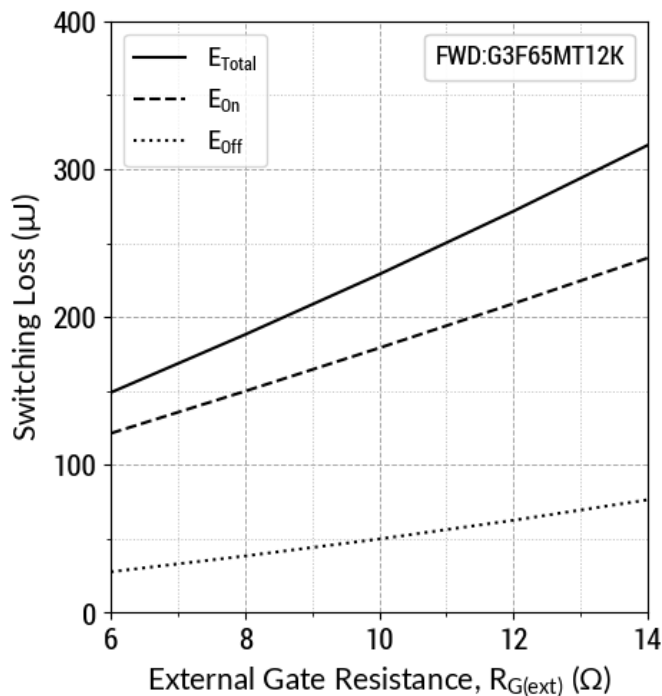
Fig 23: Typical Third Quadrant Characteristics ($T_j = -55^\circ\text{C}$)

$$I_D = f(V_{DS}, V_{GS}); t_P = 50 \mu\text{s}$$

Fig 24: Inductive Switching Energy v/s Drain Current ($V_{DD} = 800\text{V}$)

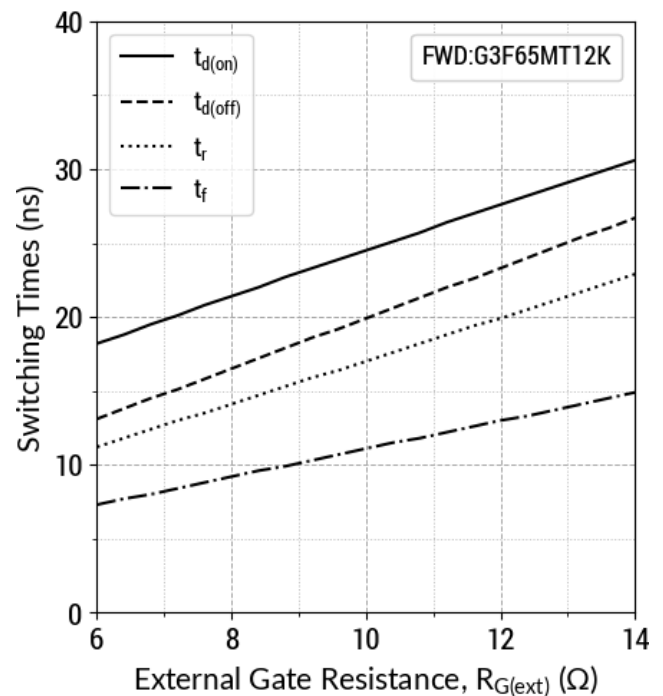
$$T_j = 25^\circ\text{C}; V_{GS} = -5/+18\text{V}; R_{G(\text{ext})} = 8 \Omega; L = 80.0 \mu\text{H}$$

Fig 25: Inductive Switching Energy v/s $R_{G(ext)}$
($V_{DD} = 800V$)



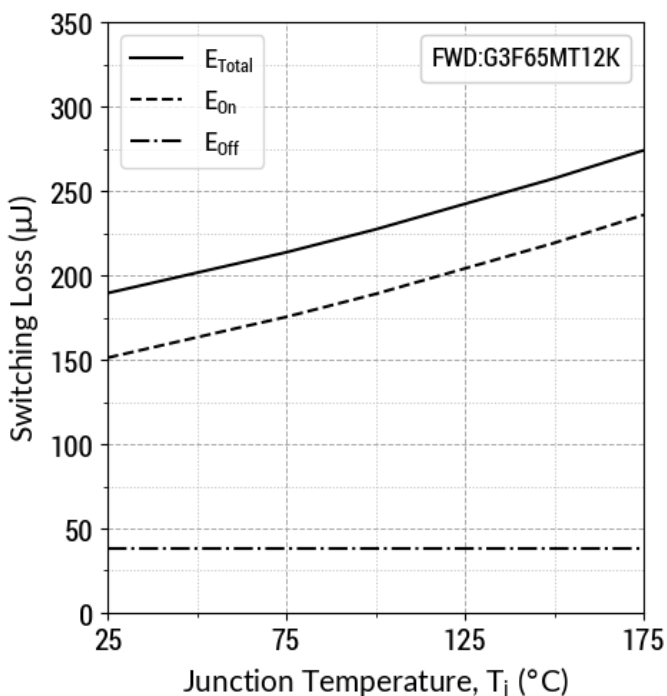
$T_j = 25^\circ C$; $V_{GS} = -5/+18V$; $I_{DS} = 15 A$; $L = 80.0\mu H$

Fig 26: Switching Time v/s $R_{G(ext)}$
($V_{DD} = 800V$)



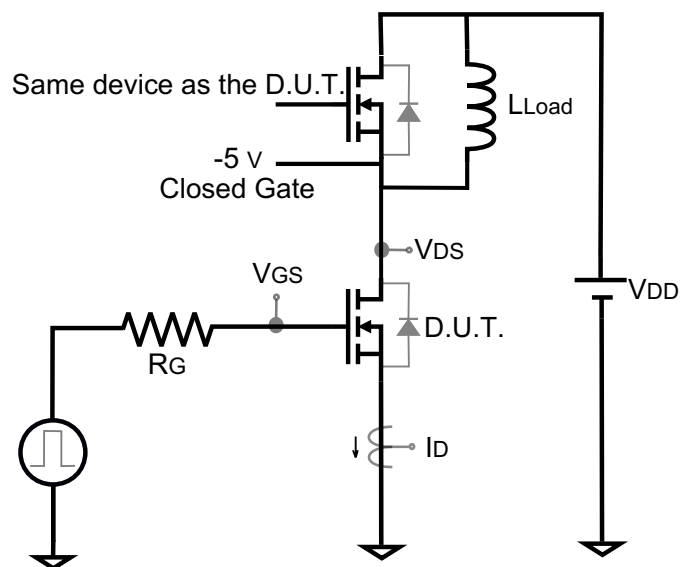
$T_j = 25^\circ C$; $V_{GS} = -5/+18V$; $I_{DS} = 15 A$; $L = 80.0\mu H$

Fig 27: Inductive Switching Energy v/s Temperature
($V_{DD} = 800V$)

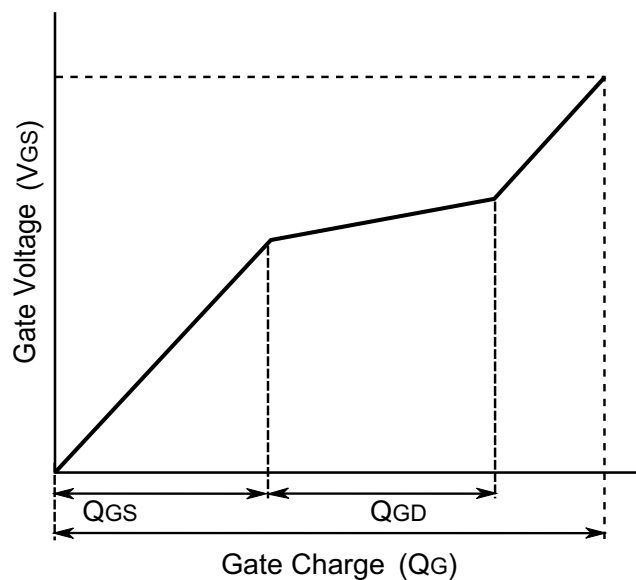


$T_j = 25^\circ C$; $V_{GS} = -5/+18V$; $R_{G(ext)} = 8 \Omega$; $I_{DS} = 15 A$; $L = 80.0\mu H$

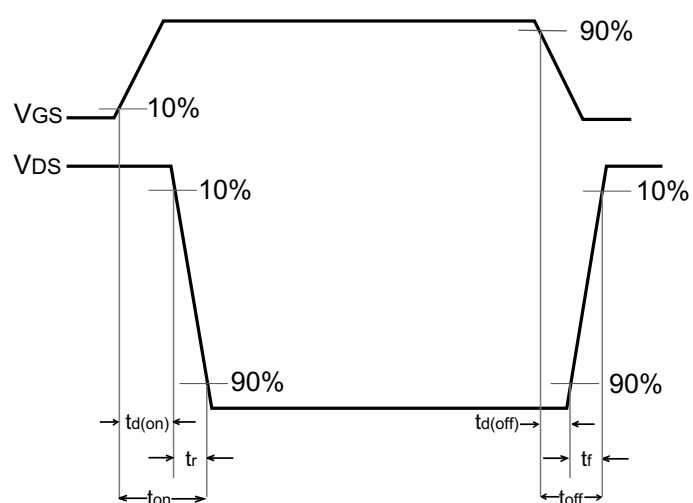
Gate Charge Waveform



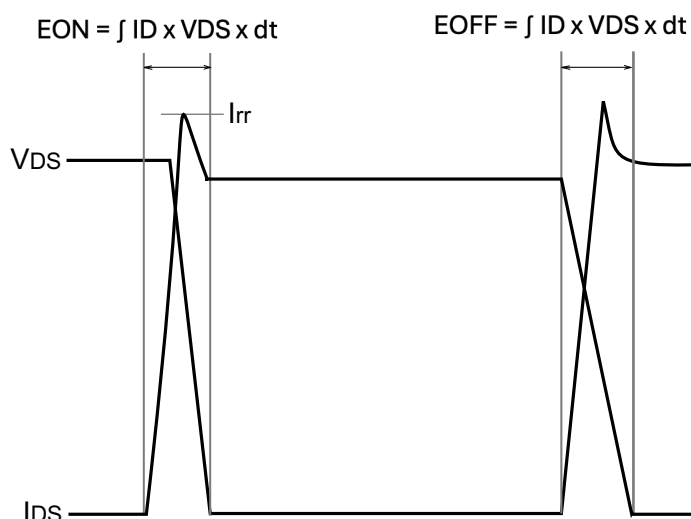
Note: Gate Charge, Switching Time and Energy Circuit



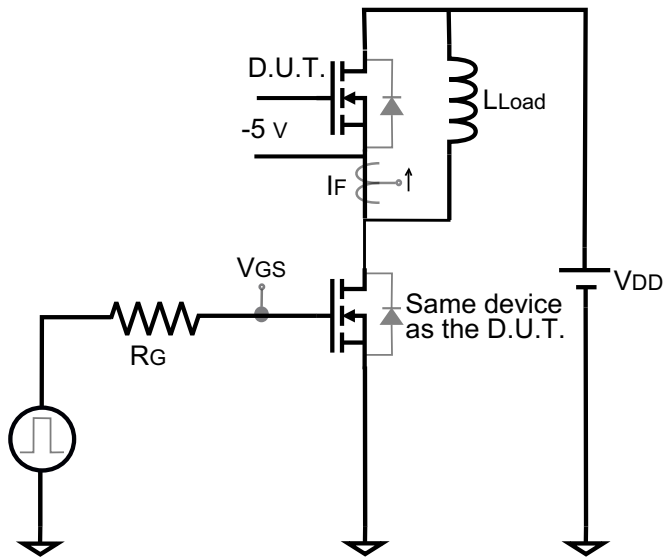
Switching Time Waveform



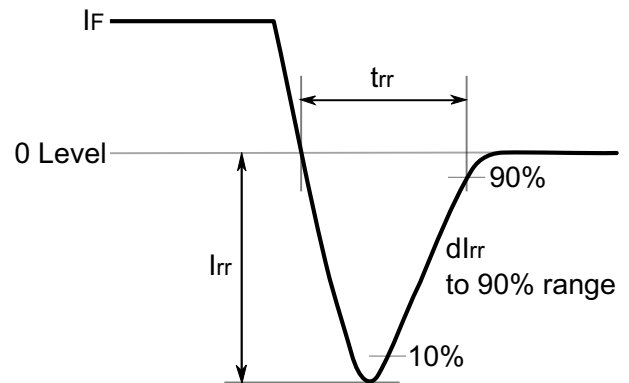
Switching Energy Waveform



Reverse Recovery Circuit

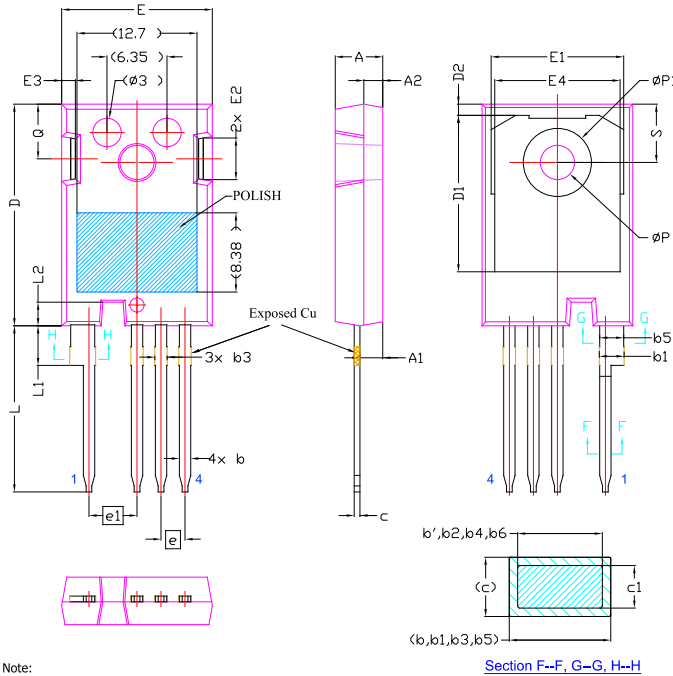


Reverse Recovery Waveform



Package Dimensions

TO-247-4 Package Outline



- Note:
1. All Dimensions Are In mm.
 2. Slot Required, Notch May Be Rounded
 3. Dimension D & E Do Not Include Mold Flash. Mold Flash Shall Not Exceed 0.127mm Pre Side. These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
 4. Thermal Pad Contour Optional Within Dimension D1 & E1.
 5. Lead Finish Uncontrolled In L1.
 6. ØP To Have A Draft Angle Of 1.5° (REF.) To The Top Of The Part With Hole Diameter Of 3.91mm (REF.).

Section F--F, G--G, H--H

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.83	5.02	5.21
A1	2.29	2.41	2.54
A2	1.91	2.00	2.16
b'	1.07	1.20	1.28
b	1.07	1.20	1.33
b1	2.39	2.67	2.94
b2	2.39	2.67	2.84
b3	1.07	1.30	1.60
b4	1.07	1.30	1.50
b5	2.39	2.53	2.69
b6	2.39	2.53	2.64
c	0.55	0.60	0.68
c1	0.55	0.60	0.65
D	23.30	23.45	23.60
D1	16.25	16.55	17.65
D2	0.95	1.19	1.25
E	15.75	15.94	16.13
E1	13.10	14.02	14.15
E2	3.68	4.40	5.10
E3	1.00	1.45	1.90
E4	12.38	13.26	13.43
e	2.54 BSC		
e1	5.08 BSC		
L	17.31	17.57	17.82
L1	3.97	4.19	4.37
L2	2.35	2.50	2.65
ØP	3.51	3.61	3.65
ØP1	7.19 REF.		
Q	5.49	5.79	6.00
S	6.04	6.17	6.30

NOTE

1. CONTROLLED DIMENSION IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.
3. THE SOURCE AND KELVIN-SOURCE PINS ARE NOT INTERCHANGABLE. THEIR EXCHANGE MIGHT LEAD TO MALFUNCTION.

Revision History

• Rev 24/Aug: Initial Release (Rev 1.0)

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